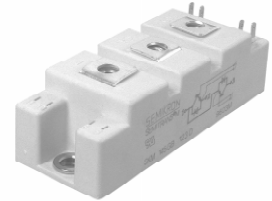


Absolute Maximum Ratings		Values	Units
Symbol	Conditions ¹⁾		
V _{CES}		1200	V
V _{CGR}	R _{GE} = 20 kΩ	1200	V
I _C	T _{case} = 25/85 °C	150 / 100	A
I _{CM}	T _{case} = 25/85 °C; t _p = 1 ms	300 / 200	A
V _{GES}		± 20	V
P _{tot}	per IGBT, T _{case} = 25 °C	700	W
T _j , (T _{stg})		-40 ... + 150 (125)	°C
V _{isol}	AC, 1 min.	2 500	V
humidity	DIN 40040	Class F	
climate	DIN IEC 68 T.1	40/125/56	
Inverse Diode			
I _F = -I _C	T _{case} = 25/80 °C	95 / 65	A
I _{FM} = -I _{CM}	T _{case} = 25/80 °C; t _p = 1 ms	300 / 200	A
I _{FSM}	t _p = 10 ms; sin.; T _j = 150 °C	720	A
I ² t	t _p = 10 ms; T _j = 150 °C	2600	A ² s

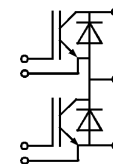
SEMITRANS® M Low Loss IGBT Modules

SKM 100 GB 124 D



SEMITRANS 2

Characteristics		min.	typ.	max.	Units
Symbol	Conditions ¹⁾				
V _{(BR)CES}	V _{GE} = 0, I _C = 4 mA	≥ V _{CES}	-	-	V
V _{GE(th)}	V _{GE} = V _{CE} , I _C = 2 mA	4,5	5,5	6,5	V
I _{CES}	V _{GE} = 0 } T _j = 25 °C	-	0,1	1,5	mA
	V _{CE} = V _{CES} } T _j = 125 °C	-	6	-	mA
I _{GES}	V _{GE} = 20 V, V _{CE} = 0	-	-	300	nA
V _{CESat}	I _C = 75 A } V _{GE} = 15 V; } T _j = 25 (125) °C	-	2,1(2,4)	2,45(2,85)	V
V _{CESat}	I _C = 100 A } T _j = 25 (125) °C	-	2,5(3,0)	-	V
g _{fs}	V _{CE} = 20 V, I _C = 75 A	31	-	-	S
C _{CHC}	per IGBT	-	-	350	pF
C _{ies}	V _{GE} = 0	-	5	6,6	nF
C _{oes}	V _{CE} = 25 V	-	720	900	pF
C _{res}	f = 1 MHz	-	380	500	pF
L _{CE}		-	-	30	nH
t _{d(on)}	V _{CC} = 600 V	-	80	-	ns
t _r	V _{GE} = -15 V / +15 V ³⁾	-	45	-	ns
t _{d(off)}	I _C = 75 A, ind. load	-	430	-	ns
t _f	R _{Gon} = R _{Goff} = 10 Ω	-	55	-	ns
E _{on} ⁵⁾	T _j = 125 °C	-	11	-	mWs
E _{off} ⁵⁾		-	9	-	mWs
Inverse Diode ⁸⁾					
V _F = V _{EC}	I _F = 75 A } V _{GE} = 0 V; } T _j = 25 (125) °C	-	2,0(1,8)	2,5	V
V _F = V _{EC}	I _F = 100 A } T _j = 25 (125) °C	-	2,25(2,05)	-	V
V _{TO}	T _j = 125 °C	-	1,1	1,2	V
r _t	T _j = 125 °C	-	-	15	mΩ
I _R RM	I _F = 75 A; T _j = 125 °C ²⁾	-	42	-	A
Q _{rr}	I _F = 75 A; T _j = 125 °C ²⁾	-	9,1	-	μC
Thermal characteristics					
R _{thjc}	per IGBT	-	-	0,18	°C/W
R _{thjc}	per diode	-	-	0,50	°C/W
R _{thch}	per module	-	-	0,05	°C/W



GB

Features

- MOS input (voltage controlled)
- N channel, homogeneous Silicon structure (NPT- Non punch-through IGBT)
- Low loss high density chip
- Low tail current
- High short circuit capability, self limiting to 6 * I_{Cnom}
- Latch-up free
- Fast & soft inverse CAL diodes ⁸⁾
- Isolated copper baseplate using DCB Direct Copper Bonding Technology without hard mould
- Large clearance (10 mm) and creepage distances (20 mm)

Typical Applications:

→ B 6 – 121

- Switching (not for linear use)

¹⁾ T_{case} = 25 °C, unless otherwise specified

²⁾ I_F = -I_C, V_R = 600 V, -di_F/dt = 800 A/μs, V_{GE} = 0 V

³⁾ Use V_{GEoff} = -5... -15 V

⁵⁾ See fig. 2 + 3; R_{Goff} = 10 Ω

⁸⁾ CAL = Controlled Axial Lifetime Technology

Cases and mech. data

→ B 6 – 122

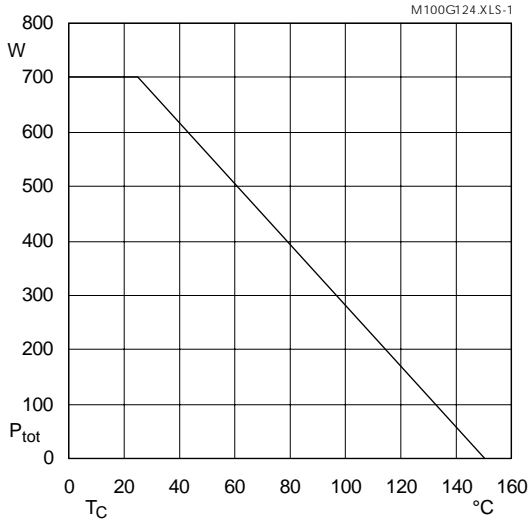


Fig. 1 Rated power dissipation $P_{tot} = f(T_C)$

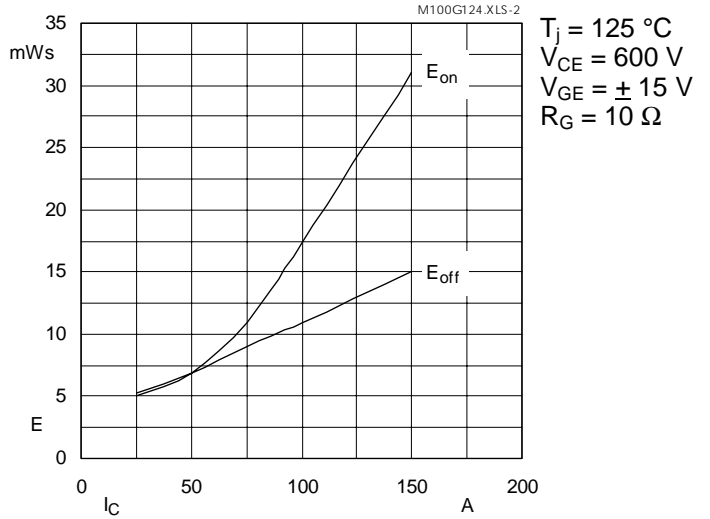


Fig. 2 Turn-on /-off energy = $f(I_C)$

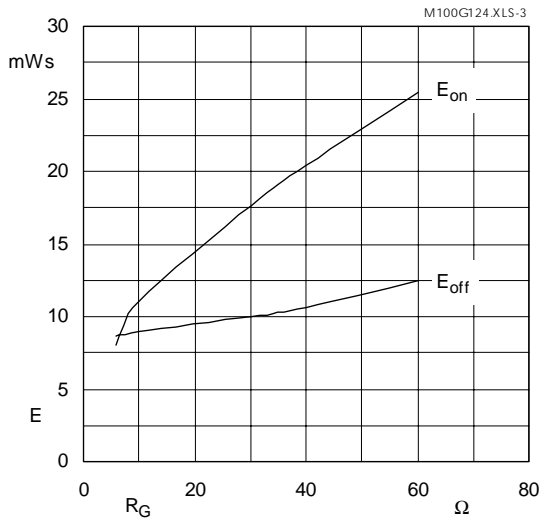


Fig. 3 Turn-on /-off energy = $f(R_G)$

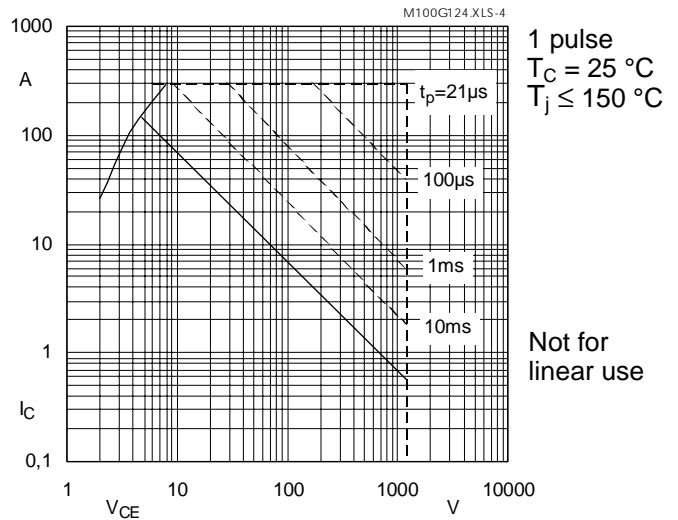


Fig. 4 Maximum safe operating area (SOA) $I_C = f(V_{CE})$

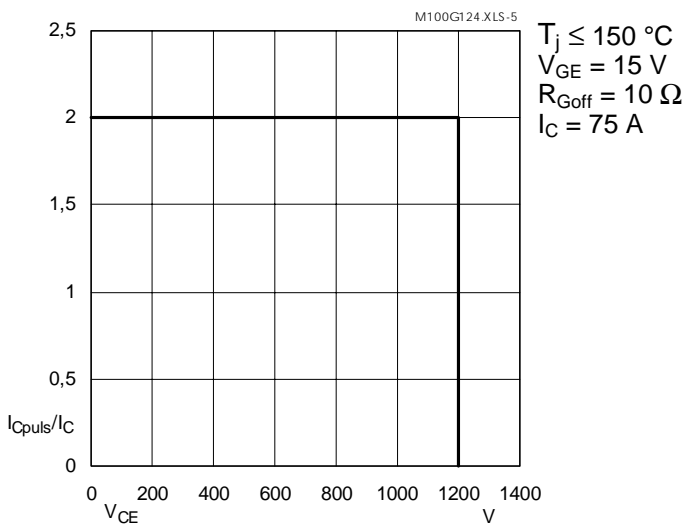


Fig. 5 Turn-off safe operating area (RBSOA)

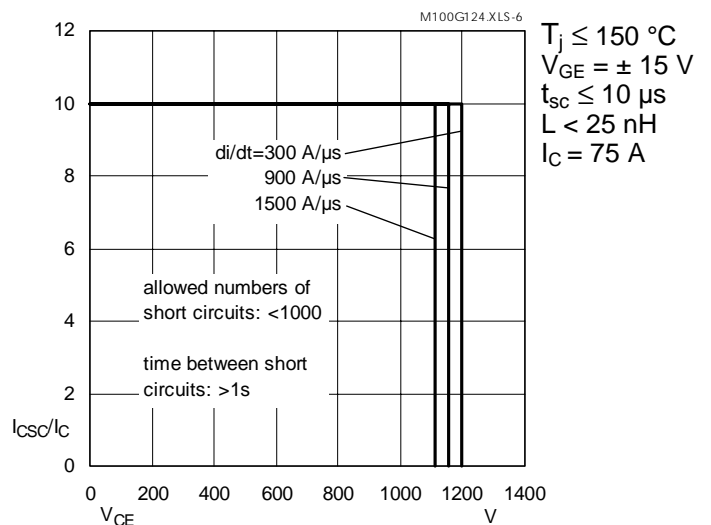


Fig. 6 Safe operating area at short circuit $I_C = f(V_{CE})$

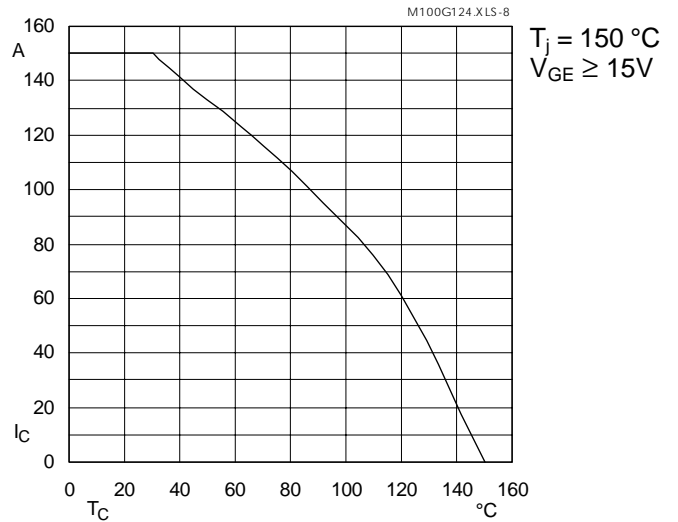


Fig. 8 Rated current vs. temperature $I_C = f(T_C)$

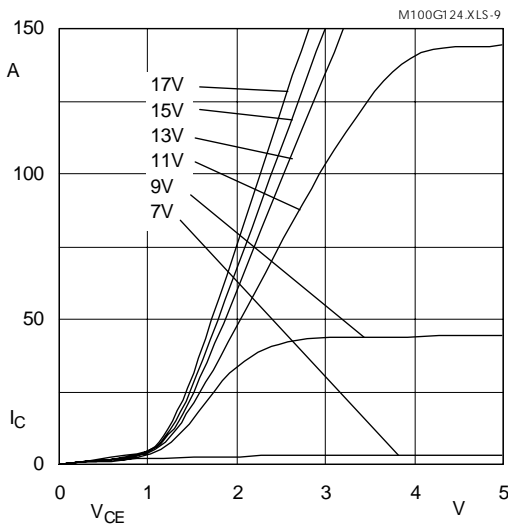


Fig. 9 Typ. output characteristic, $t_p = 80\text{ }\mu\text{s}$; $25\text{ }^\circ\text{C}$

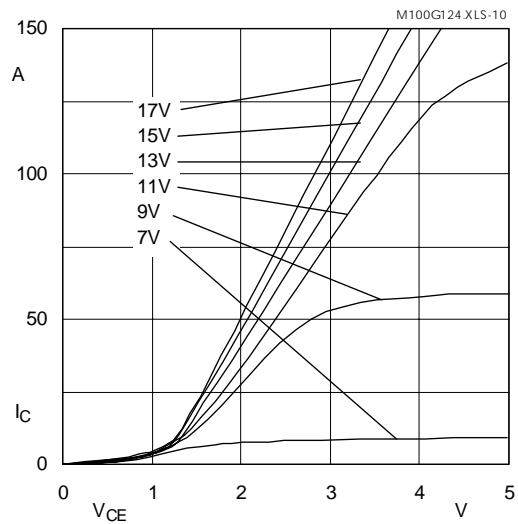


Fig. 10 Typ. output characteristic, $t_p = 80\text{ }\mu\text{s}$; $125\text{ }^\circ\text{C}$

$$P_{\text{cond}(t)} = V_{\text{CEsat}(t)} \cdot I_{\text{C}(t)}$$

$$V_{\text{CEsat}(t)} = V_{\text{CE(TO)(Tj)}} + r_{\text{CE(Tj)}} \cdot I_{\text{C}(t)}$$

$$V_{\text{CE(TO)(Tj)}} \leq 1,3 + 0,0005 (T_j - 25) \text{ [V]}$$

$$\text{typ.: } r_{\text{CE(Tj)}} = 0,0107 + 0,000033 (T_j - 25) \text{ [\Omega]}$$

$$\text{max.: } r_{\text{CE(Tj)}} = 0,0153 + 0,000047 (T_j - 25) \text{ [\Omega]}$$

$$\text{valid for } V_{\text{GE}} = +15 \pm 2_{-1} \text{ [V]; } I_C > 0,3 I_{\text{Cnom}}$$

Fig. 11 Saturation characteristic (IGBT)
Calculation elements and equations

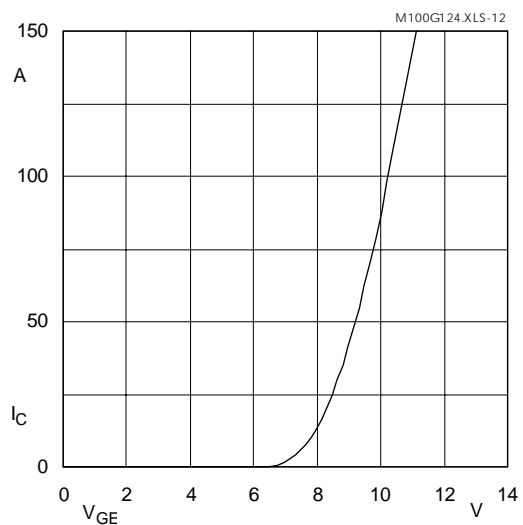


Fig. 12 Typ. transfer characteristic, $t_p = 80\text{ }\mu\text{s}$; $V_{CE} = 20\text{ V}$

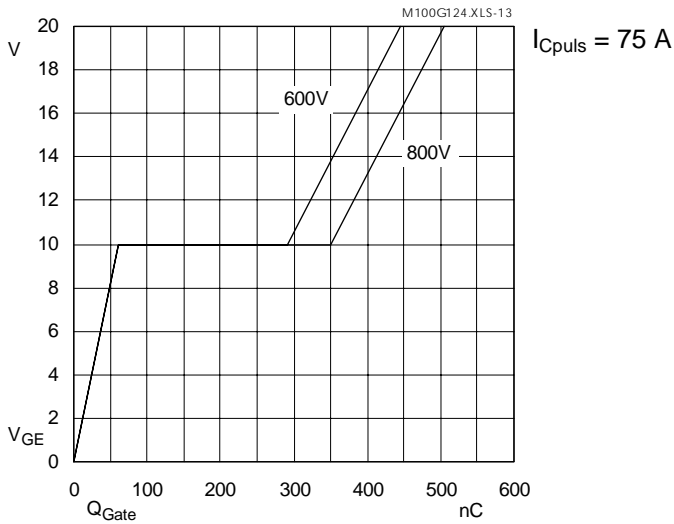


Fig. 13 Typ. gate charge characteristic

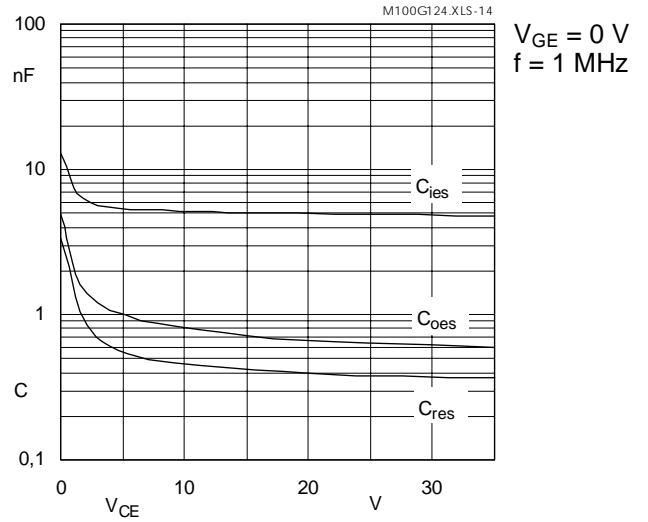


Fig. 14 Typ. capacitances vs. V_{CE}

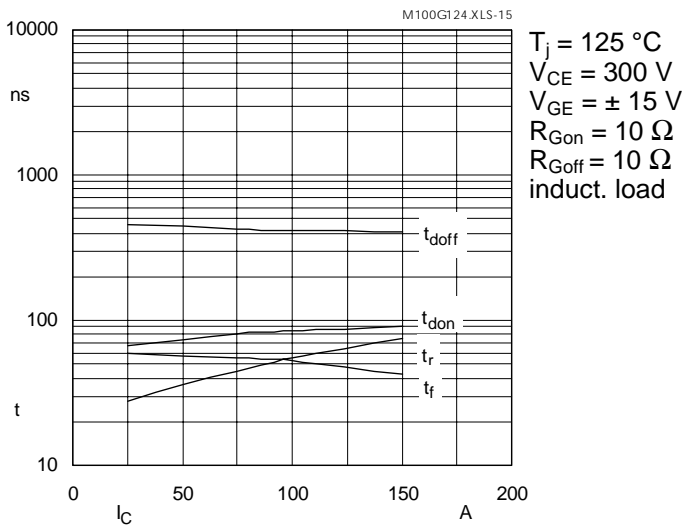


Fig. 15 Typ. switching times vs. I_C

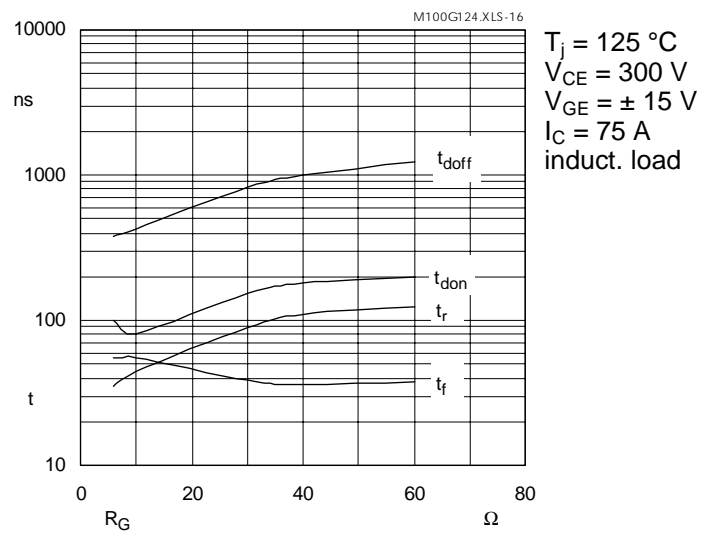


Fig. 16 Typ. switching times vs. gate resistor R_G

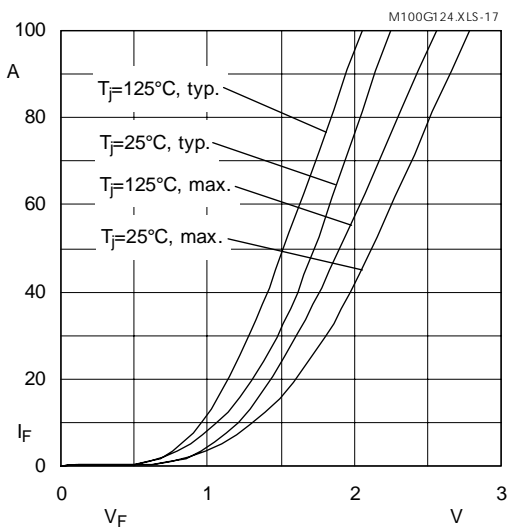


Fig. 17 Typ. CAL diode forward characteristic

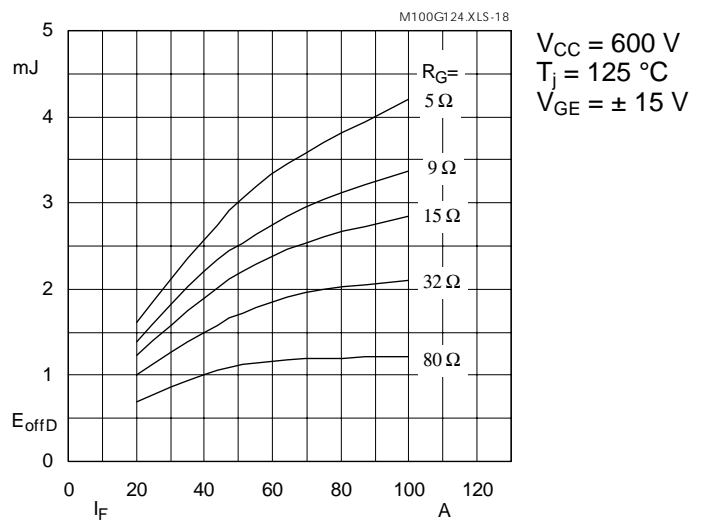


Fig. 18 Diode turn-off energy dissipation per pulse

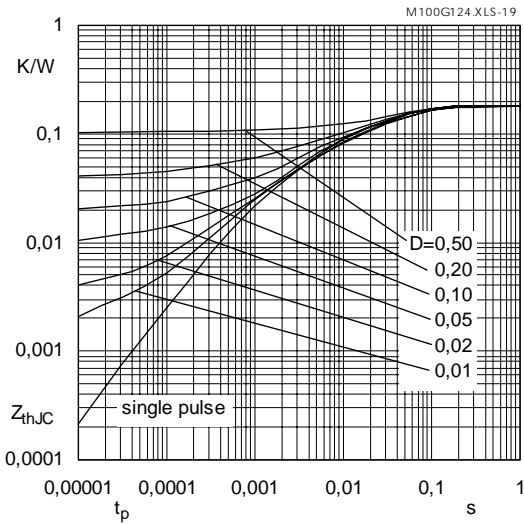


Fig. 19 Transient thermal impedance of IGBT
 $Z_{thJC} = f(t_p)$; $D = t_p / t_c = t_p \cdot f$

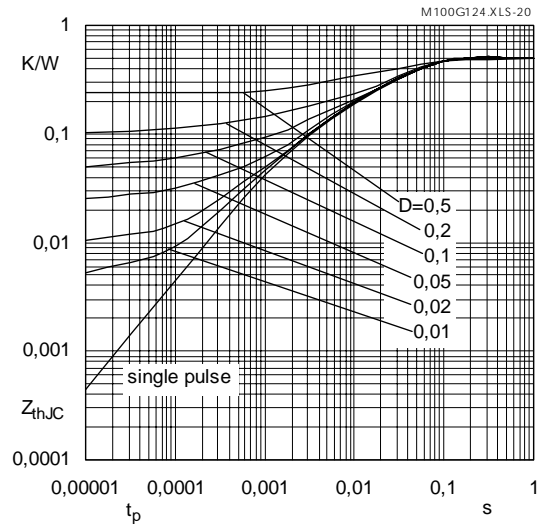


Fig. 20 Transient thermal impedance of inverse CAL diodes

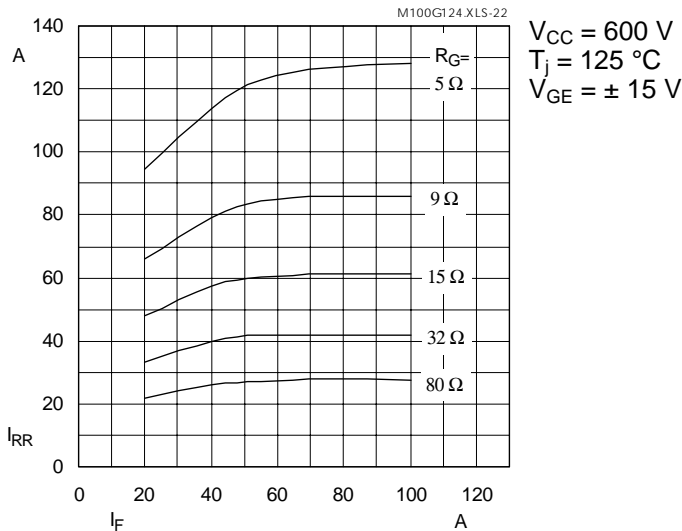


Fig. 22 Typ. CAL diode peak reverse recovery current $I_{RR} = f(I_F; R_G)$

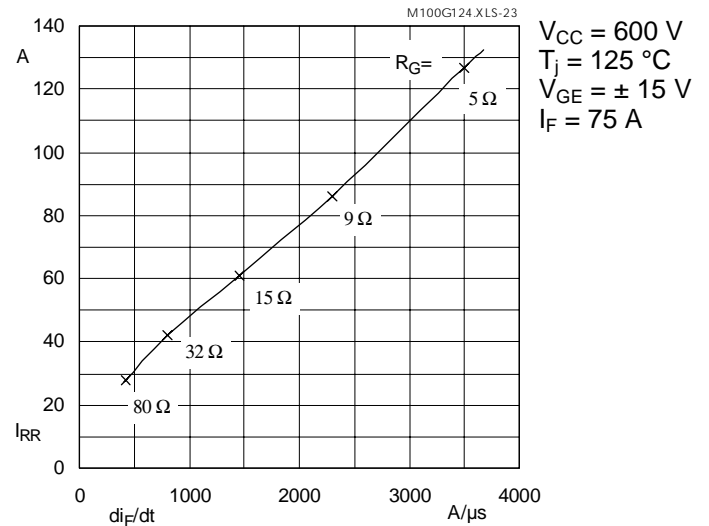


Fig. 23 Typ. CAL diode peak reverse recovery current $I_{RR} = f(di_F/dt)$

Typical Applications

include

- Switched mode power supplies
- DC servo and robot drives
- Inverters
- DC choppers
- AC motor speed control
- UPS Uninterruptable power supplies
- General power switching applications

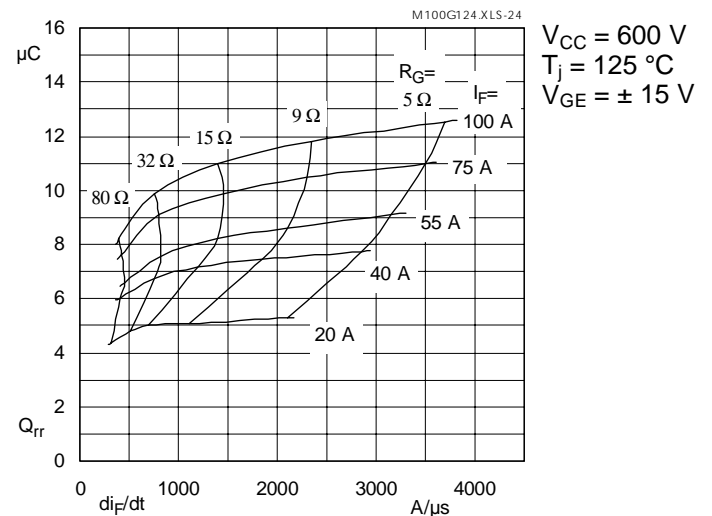
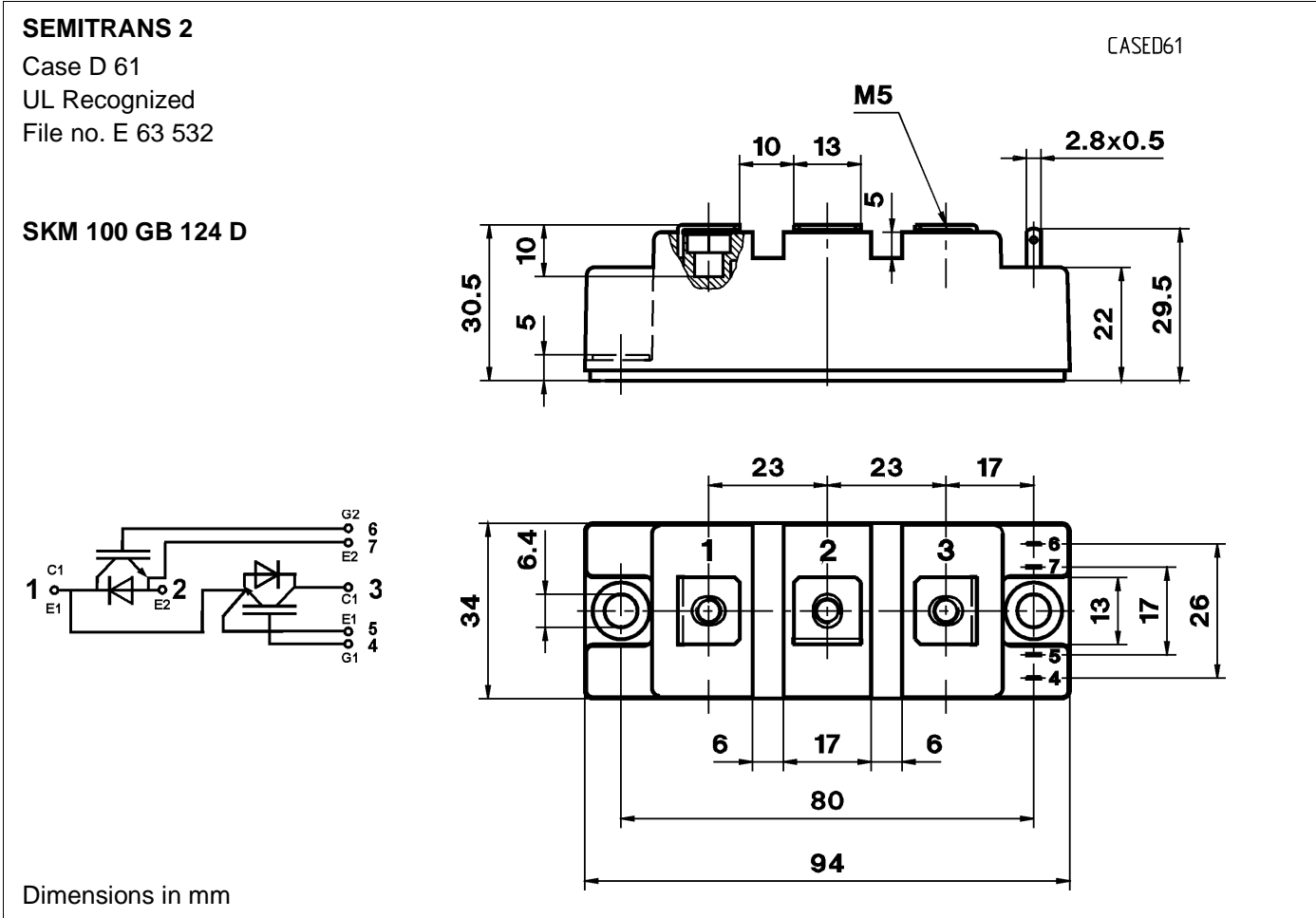


Fig. 24 Typ. CAL diode recovered charge

SKM 100 GB 124 D



Case outline and circuit diagram

Mechanical Data			Values			Units
Symbol	Conditions		min.	typ.	max.	
M ₁	to heatsink, SI Units (M6)		3	–	5	Nm
	to heatsink, US Units		27	–	44	lb.in.
M ₂	for terminals, SI Units (M5)		2,5	–	5	Nm
	for terminals, US Units		22	–	44	lb.in.
a			–	–	5x9,81	m/s ²
w			–	–	160	g

This is an electrostatic discharge sensitive device (ESDS). Please observe the international standard IEC 747-1, Chapter IX.

Eight devices are supplied in one SEMIBOX A without mounting hardware, which can be ordered separately under Ident No. 33321100 (for 10 SEMITRANS 2)

Larger packing units of 20 or 42 pieces are used if suitable
 Accessories → B 6 – 4
 SEMIBOX → C – 1.